

# Felix CÃ¼ppers

## List of Publications by Year in descending order

Source: <https://exaly.com/author-pdf/3333988/publications.pdf>

Version: 2024-02-01

9  
papers

438  
citations

1307594

7  
h-index

1720034

7  
g-index

9  
all docs

9  
docs citations

9  
times ranked

478  
citing authors

#	ARTICLE	IF	CITATIONS
1	NEUROTEC I: Neuro-inspired Artificial Intelligence Technologies for the Electronics of the Future. , 2022, , .		0
2	Utilizing the Switching Stochasticity of HfO <sub>2</sub> /TiO <sub>x</sub> -Based ReRAM Devices and the Concept of Multiple Device Synapses for the Classification of Overlapping and Noisy Patterns. <i>Frontiers in Neuroscience</i> , 2021, 15, 661856.	2.8	26
3	Reliability Aspects of Memristive Devices for Computation-in-Memory Applications. , 2021, , .		0
4	Intrinsic RESET Speed Limit of Valence Change Memories. <i>ACS Applied Electronic Materials</i> , 2021, 3, 5563-5572.	4.3	15
5	Variability-Aware Modeling of Filamentary Oxide-Based Bipolar Resistive Switching Cells Using SPICE Level Compact Models. <i>IEEE Transactions on Circuits and Systems I: Regular Papers</i> , 2020, 67, 4618-4630.	5.4	72
6	Design of defect-chemical properties and device performance in memristive systems. <i>Science Advances</i> , 2020, 6, eaaz9079.	10.3	65
7	Exploiting the switching dynamics of HfO <sub>2</sub> -based ReRAM devices for reliable analog memristive behavior. <i>APL Materials</i> , 2019, 7, .	5.1	94
8	Improved Switching Stability and the Effect of an Internal Series Resistor in HfO <sub>2</sub> /TiO <sub>x</sub> Bilayer ReRAM Cells. <i>IEEE Transactions on Electron Devices</i> , 2018, 65, 3229-3236.	3.0	95
9	Understanding the Coexistence of Two Bipolar Resistive Switching Modes with Opposite Polarity in Pt/TiO <sub>2</sub> /Ti/Pt Nanosized ReRAM Devices. <i>ACS Applied Materials &amp; Interfaces</i> , 2018, 10, 29766-29778.	8.0	71